

WHAT IS CLAIMED IS:

1. A semiconductor laser device, which is provided with an active layer and a first clad layer on a substrate and provided with a ridge section constructed of a second clad layer and upper layers including a cap layer on the
5 first clad layer,

the upper layer protruding in both widthwise directions beyond the second clad layer, providing a step of not smaller than 0.13 mm between the upper layers and
10 the second clad layer.

2. The semiconductor laser device as claimed in claim 1, wherein

a current constriction layer is provided on both sides of the ridge section, and a portion of the current
15 constriction layer, the portion being located outside a portion brought in contact with the ridge section and having surfaces formed flatly, is formed to have a thickness smaller than a thickness of the second clad layer of the ridge section.

20 3. The semiconductor laser device as claimed in claim 1, wherein

a portion of the current constriction layer brought in contact with the ridge section has a thickness of not smaller than half a thickness of the second clad
25 layer of the ridge section.

4. The semiconductor laser device as claimed in claim 1, wherein

the substrate is an inclined substrate.

5. A semiconductor laser device manufacturing method comprising the steps of:

forming at least an active layer, a first clad layer, a second clad layer and upper layers including a cap layer on a substrate; and

forming a ridge section comprised of the second clad layer and the upper layers by subjecting the second clad layer and the upper layers to dry etching and subsequently to wet etching.

6. The semiconductor laser device manufacturing method as claimed in claim 5, wherein

a step is formed between the upper layers and the second clad layer by making the upper layers protrude in both widthwise directions beyond the second clad layer by wet etching.